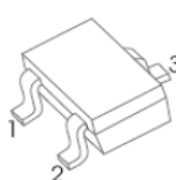


<b>TRANSISTOR (NPN)</b>	<b>SOT-323 Plastic-Encapsulate Transistors</b>
<p><u>SOT-323</u></p>  <p>1. BASE 2. EMITTER 3. COLLECTOR</p>	<p><b>Features</b></p> <p>Complimentary to SS8550W</p>

**MAXIMUM RATINGS (T<sub>a</sub>=25°C unless otherwise noted)**

Symbol	Parameter	Value	Unit
V <sub>CB0</sub>	Collector-Base Voltage	40	V
V <sub>CEO</sub>	Collector-Emitter Voltage	25	V
V <sub>EBO</sub>	Emitter-Base Voltage	5	V
I <sub>C</sub>	Collector Current	1.5	A
P <sub>C</sub>	Collector Power Dissipation	250	mW
R <sub>θJA</sub>	Thermal Resistance From Junction To Ambient	500	°C/W
T <sub>J</sub> , T <sub>stg</sub>	Operation Junction and Storage Temperature Range	-55~+150	°C

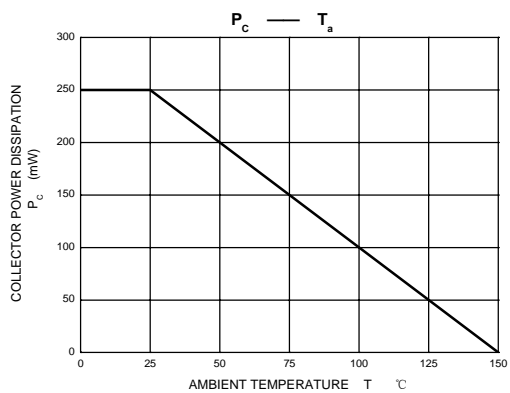
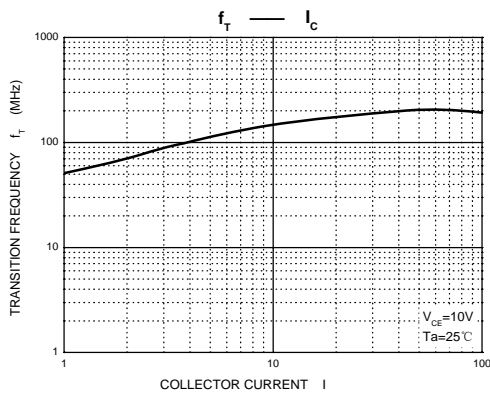
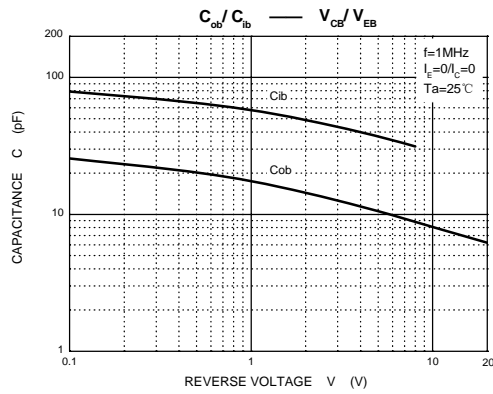
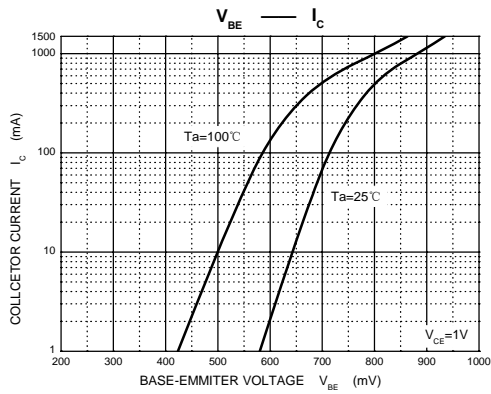
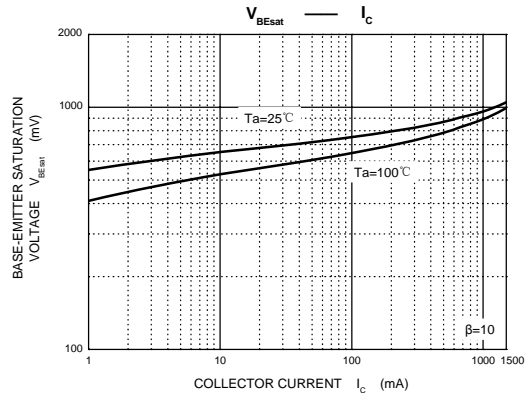
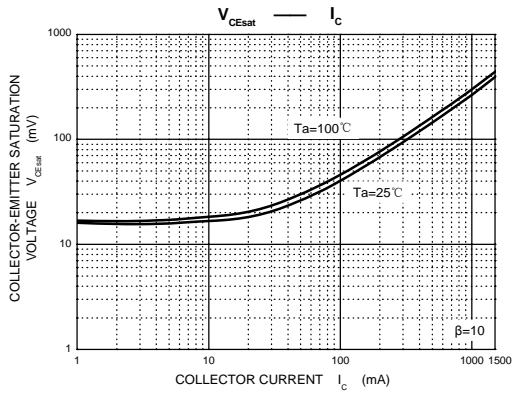
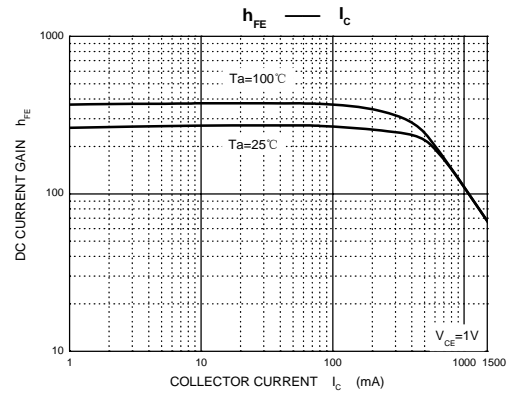
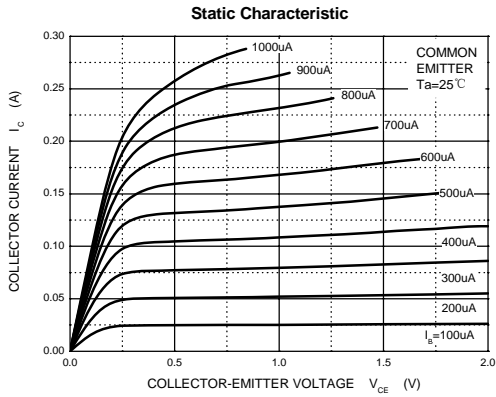
**ELECTRICAL CHARACTERISTICS (T<sub>a</sub>=25°C unless otherwise specified)**

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V <sub>(BR)CBO</sub>	I <sub>C</sub> = 100μA, I <sub>E</sub> =0	40			V
Collector-emitter breakdown voltage	V <sub>(BR)CEO</sub>	I <sub>C</sub> = 0.1mA, I <sub>B</sub> =0	25			V
Emitter-base breakdown voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> =100μA, I <sub>C</sub> =0	5			V
Collector cut-off current	I <sub>CB0</sub>	V <sub>CB</sub> =40V, I <sub>E</sub> =0			0.1	μA
Collector cut-off current	I <sub>CEO</sub>	V <sub>CE</sub> =20V, I <sub>E</sub> =0			0.1	μA
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> = 5V, I <sub>C</sub> =0			0.1	μA
DC current gain	h <sub>FE(1)</sub>	V <sub>CE</sub> =1V, I <sub>C</sub> = 100mA	120		400	
	h <sub>FE(2)</sub>	V <sub>CE</sub> =1V, I <sub>C</sub> = 800mA	40			
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =800mA, I <sub>B</sub> = 80mA			0.5	V
Base-emitter saturation voltage	V <sub>BE(sat)</sub>	I <sub>C</sub> =800mA, I <sub>B</sub> = 80mA			1.2	V
Transition frequency	f <sub>T</sub>	V <sub>CE</sub> =10V, I <sub>C</sub> = 50mA, f=30MHz	100			MHz
Collector output capacitance	C <sub>ob</sub>	V <sub>CB</sub> =10V, I <sub>E</sub> =0, f=1MHz			15	pF

**CLASSIFICATION OF h<sub>FE(1)</sub>**

Rank	L	H	J
Range	120-200	200-350	300-400

**Typical Characteristics**



单击下面可查看定价，库存，交付和生命周期等信息

[>>DIOS\(迪恩思\)](#)